

IN THE CLAIMS:

Please amend claim 1 as follows. A marked version of the amended claim appears in appendix A attached hereto. Please cancel non-elected claims 11-19 without prejudice or disclaimer of the subject matter contained therein. Please add new claim 20.

1. (amended) A semiconductor device comprising:
a source and a drain, said source and drain consisting essentially of silicide;
a semiconductor body disposed between the source and the drain;
a gate electrode disposed over the body and defining a channel interposed between the source and the drain; and
a gate dielectric made from a high-K material and separating the gate electrode and the body.

20. (new) The semiconductor device according to claim 1, wherein a source/body junction is defined by silicide material of the source and semiconductor material of the body and a drain/body junction is defined by silicide material of the drain and semiconductor material of the body.
